ABSTRACT

A wafer, exposure mask, method for detecting an alignment mark and method for exposure, which make it possible to improve accuracy of the alignment as well as correction of a gap between the wafer and the exposure mask, are provided. There is provided a wafer having alignment marks (wafer marks) with edges for causing inspection light for alignment to scatter at an exposure surface during proximity exposure. The wafer mark is characterized by having dot pattern groups, which are made up of dot patterns arrayed in a predetermined direction. The dot pattern group is configured by arranging dot patterns in Direction X with an arrangement interval P2. The arrangement interval P2 is wider than an arrangement interval P1 for the dot patterns. Further, there is provided an exposure mask, which is used in similar proximity exposure, having alignment marks, as mask marks, which have a similar configuration as that of the wafer marks.